

DOCKET NO: 0039-7684-2SRD DIV

21/A
Pre
Amends
812-60
C. Cant

IN THE UNITED STATES PATENTS & TRADEMARKS OFFICE

IN RE APPLICATION OF:

Hisako AOYAMA, et al.

:EXAMINER:

SERIAL NO: New Div. Application

FILED: HEREWITH

:GROUP ART UNIT:

FOR: SEMICONDUCTOR DEVICE
AND PROCESS OF FABRICATING
THE SAME

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, DC 20231

SIR:

Prior to examination on the merits, please amend the above-identified Divisional Application, filed under Rule 53(b), as follows:

IN THE CLAIMS

Please cancel without prejudice claims 1-27.

Please add new claim 28 as follows:

--28. A process of fabricating a semiconductor device comprising the steps of:

forming a first insulating film on a semiconductor substrate;

forming a second insulating film on said first insulating film, said second insulating film being made of a material different from that of the first insulating film and having a thickness smaller than that of the first insulating film;

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Amends
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